

John Payne's Contributions to the Front End Local Oscillator Effort

The Golden Year

Presented by: Skip Thacker

The Golden Year



- In 2003 John Payne served a one year temporary appointment as "LO Coordinator"
- Coordinated the efforts of Bill Shillue's photonics group in Tucson, the FELO Group's efforts in Charlottesville, Clint Janes' efforts in Socorro and Larry D'Addarrio efforts.
- John put in place a management structure that has allowed the FELO Group to produce what I will describe to you in the rest of this talk.
- I would like to emphasize that everybody at that time, both the upper management and the people who worked for John, agreed that John had done an excellent job of coordinating the LO efforts and had indeed solved many problems.



Offset Generator

Desired Features



- Photonic reference
 - New Technology
- Highly Coherent
 - 80% Coherent at 950 GHz
 - Usable to 1.2 TeraHertz
- Electrically tunable
 - Major technical consequences
- Amplitude stable
 - Suitable for Total Power radiometry as well as interferometery
- Adequate power at 950 GHz
- Phase stable
 - Factor of 200 better than EVLA
 - Factor of 50 better than SMA

Phase Stability



- 12.5 FemtoSeconds over 300 seconds
- 3.75 micron (in air)
 - This is about 0.15 mil for the non-metric folks
- For a 1 degree Centigrade change of temperature the following represent 12.5 fS.
 - Brass Waveguide approx 1.5 cm
 - SMF Fiber 40 cm
 - IF Coax at 12 GHz 35 cm



Test Data through 15 km Fiber



Phase Drift Measurements



- Increase T(WCA #1) while keeping T(WCA#2) constant
- 0.81 degrees/°C at 93.6 GHz => 24.2 fs/°C
- Max. $\Delta T(5 \text{ minutes}) = 0.083 \ ^{\circ}C => 2.0 \ \text{fs max. drift in 5 minutes}$



Sideband Noise: Band 9

LO = 678 GHz



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Custom MMICs for the ALMA Local Oscillator Subsystem





26-October-2006, Charlottesville



Power Amplifiers (PA)





- Band 3 (92-108 GHz): 0.1 μm InP HEMT
- Band 6 (73-89 GHz): 0.1 μm GaAs pHEMT
- Band 7 (94-122 GHz): 0.1 μm InP HEMT
- Band 9 (67-79 GHz): 0.1 μm GaAs PHEMT
- (Band 9 original topology: 121-143 GHz)
- 0.1 μm GaAs pHEMT gain drops above 100 GHz, usable to 110 GHz



2-Chip PA





The edge of this metal rectangle should align with the edge of the channel in the block as shown by the dashed line.

No epoxy should be underneath the part of WR8L1 which hangs over the edge of the channel.



• From FEND-40.10.07.08-002-A-PRO, "Band 7 PA Microassembly Procedures" John Payne Symposium 26-October-2006, Charlottesville



MMIC Power Amplifier for Bands 4, 8, and 9



MMIC Chip: Technology (foundry): Dimensions: Frequency: Output Power: Small-Signal Gain: Large-Signal Gain:

MMPA75 0.1 µm GaAs pHEMT (BAE) 2.8 x 1.8 x 0.050 mm 65 – 85 GHz 80 mW 14 dB 9 dB

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Output power and tuning range: Band 6-5

- 73.7-88.3 GHz
- 5-20 mW in steps of 0.5 dB or less.

LO6-5 (VD1=VD2=2.83V)







Thank You John